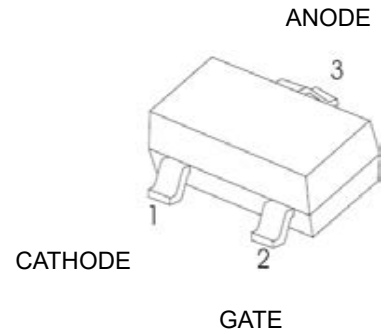




### PCR606 Silicon Planar DBDB Thyristor

#### MAIN FEATURES

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current	0.6	A
$V_{DRM}$	Repetitive peak offstate voltage	600	V
$T_j$	Junction Temperature	-40~+125	°C
$T_{stg}$	Storage Temperature	-40~+150	°C



#### SOT-23

#### DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

#### FEATURES

- RMS on-state current to 0.6 A
- General purpose switching

#### APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays

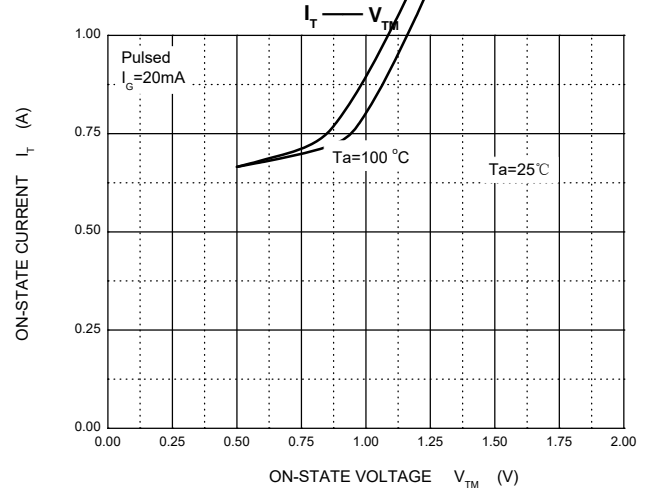
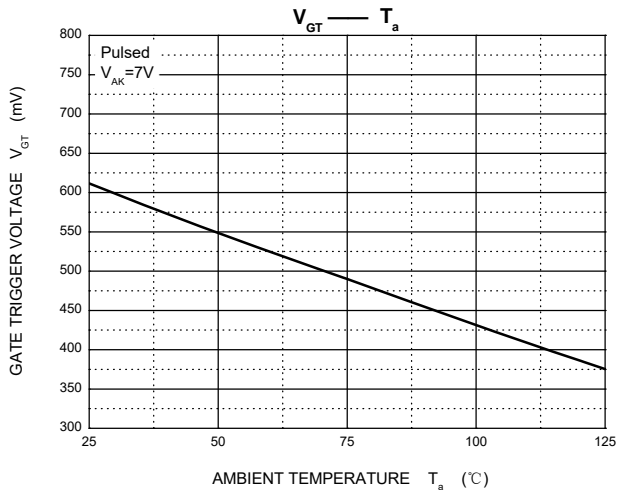
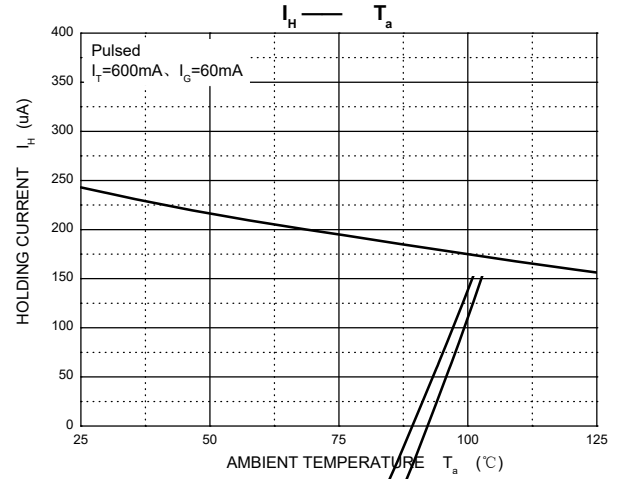
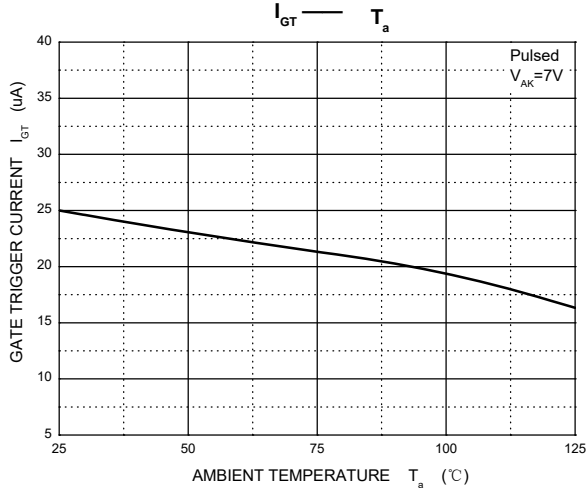
A5F?B; .6\$\*

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
On state voltage	$V_{TM}$	$I_{TM}=0.6A$		1.7	V
Gate trigger voltage	$V_{GT}$	$V_{AK}=7V$		0.8	V
Repetitive peak off-state voltage	$V_{DRM}$	$I_{DRM}=10\mu A$	600		V
Holding current	$I_H$	$I_T=600mA, I_G=60mA$		5	mA
Gate trigger current	$I_{GT}$	$V_{AK}=7V$	5	40	$\mu A$



## Typical Characteristics

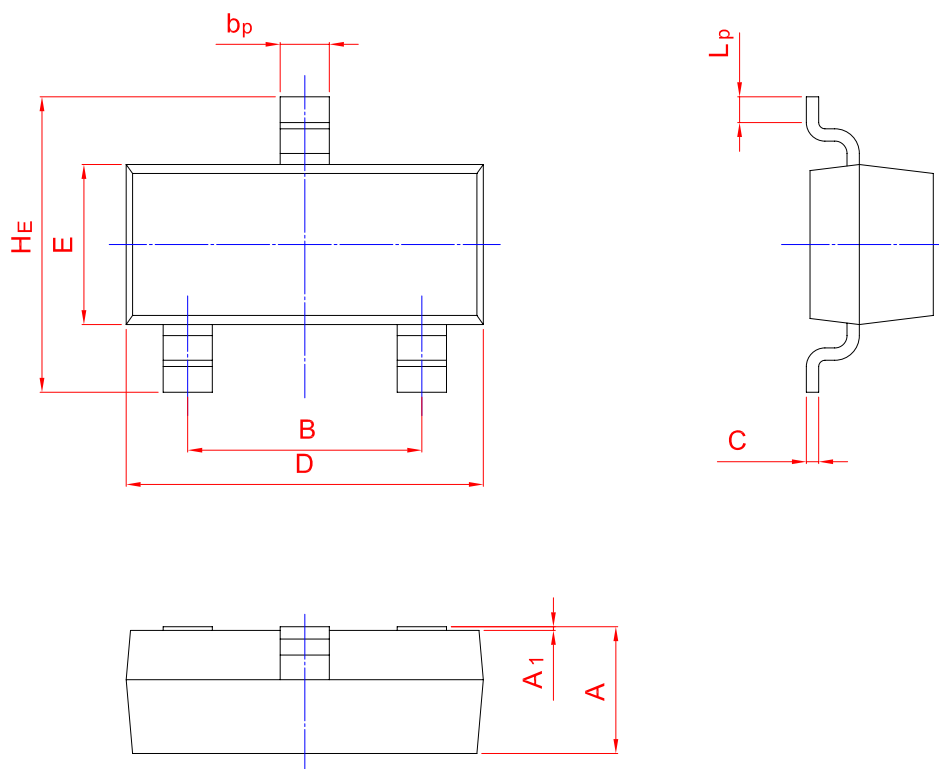
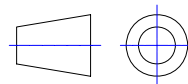




## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	He	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20